

In the Specification:

Please insert the following paragraph at page 1, line 3;

This application claims the benefit of International Patent Application No. PCT/JP03/09547 filed July 28, 2003, which claims priority of Japanese Patent Application No. 220161/2002, filed July 29, 2002.

Please amend the paragraph beginning at page 28, line 18, as indicated below;

Fig. 20C ~~23C~~ is a diagram showing a synthetic magnetic field H_{2x} applied to the ferri-magnetic laminate structure corresponding to the memory cell connected to the non-selected word line and the selected bit line;

Please amend the paragraph beginning at page 36, line 14, as indicated below;

With reference to Fig. 7A, the film thickness t of the non-magnetic spacer layer 32 of the ferri-magnetic spacer layer 32 of the ferri-magnetic laminate structure 30 is determined such that the first magnetic layer 31 is anti-ferromagnetically coupled to the second magnetic layer 33. Therefore, in the state that the magnetic field is not applied the ferri-magnetic laminate structure 30, the first magnetic layer and the ~~third~~ second magnetic layer 33 have spontaneous polarizations whose directions are opposite to each other, as shown in Fig. 7C. Also, the first magnetic layer 31 is anti-ferromagnetically coupled to the second magnetic layer 33. In this state, the total magnitude of magnetization of the ferri-magnetic laminate structure 30 is substantially 0. That is, in the state that the magnetic field is not applied to the ferri-magnetic laminate structure 30, the ferri-magnetic laminate structure 30 does not have a magnetic moment substantially. It is preferable that the ferri-magnetic laminate structure 30 does not have the magnetic moment as a whole, a magnetic field generated by the magnetic moment is applied to the magneto-resistance element 7. Therefore, in the state that the currents I_x and I_y are not supplied to the selected write word line and the selected bit line, the magnetic field generated by the magnetic moment is applied to the magneto-resistance element 7. This magnetic field makes a reversing magnetic field (coercive force) where the spontaneous magnetization of the free layer 28 of the magneto-resistance element 7 is reversed asymmetrical, so that the magneto-resistance element 7 has the offset magnetic field. It is not preferable since an existence of the offset magnetic field. It is not preferable since an existence of the offset magnetic field applied to the magneto-resistance element 7 increases the write

currents I_x and I_y , and an operation margin of the memory cell 2 is decreased. The ferromagnetic laminate structure 30 which does not have the magnetic moment effectively prevents the generation of the offset magnetic field in the magneto-resistance element 7.